

# **SEARCH REQUEST FORM**

# Scientific and Technical Information Center

Requester's Full Name: Art Unit: <i>l 795</i> Pho Mail Box-and Bldg/Room-Loo			Examiner # Serial ults Format P	: 7663 Number: referred (circle):	Date: 1-9- 10/563,50 PAPER DISK	-0 <i>B</i> 21_ E-MAIL	
f more than one search is s		ase prioriti	ze searches ******	in order of ne	ed. *******	*****	
Please provide a detailed statement of include the elected species or structualitity of the invention. Define any known. Please attach a copy of the control	ares, keywords, s terms that may ha	ynonyms, acro ive a special m	nyms, and regist eaning. Give ex	ry numbers, and c	ombine with the cond	ept or	
Title of Invention:	P17.	Del B	3. b.				
nventors (please provide full nam	es):					<del></del>	
Earliest Priority Filing Date: _							
*For Sequence Searches Only* Please appropriate serial number.	include all pertine	ent information	(parent, child, div	visional, or issued po	ntent numbers) along w	ith the	
Please	search	, for	the	Polymers	of		
a. #1							

SCIENTIFIC REFERENCE BR
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Pat. & T.M Office

STAFF USE ONLY	Type of Search	Vendors and cost where applicable
Searcher: EX	NA Sequence (#)	STN
Searcher Phone #:	AA Sequence (#)	Dialog
Searcher Location:	Structure (#)	Questel/Orbit
Date Searcher Picked Up:	Bibliographic	Dr.Link
Date Completed: 1-15-08	Litigation	Lexis/Nexis
Searcher Prep & Review Time:	Fulltext	Sequence Systems
Clerical Prep Time:	Patent Family	WWW/Internet
Online Time:	Other ·	Other (specify)
PTO-1590 (8-01)		,,

Appl. No. : Unknown Filed : Herewith

# AMENDMENTS TO THE CLAIMS

1. (Original) A polymer comprising at least one structural unit (a1) containing a lactone represented by one of general formulas (1) through (4) shown below:

(wherein, in said formulas (1) to (4), R represents a hydrogen atom or a methyl group, and m is either 0 or 1).

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=> D HIS

FILE 'LREGISTRY' ENTERED ON 15 JAN 2008

L1 STR

FILE 'REGISTRY' ENTERED ON 15 JAN 2008

L2 SCR 2043

L3 1 S L1 AND L2

L4 25 S L1 AND L2 FUL SAV L4 LEE501/A

FILE 'ZCA' ENTERED ON 15 JAN 2008

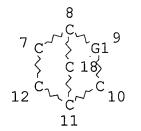
L5 15 S L4

L6 6 S 1840-2003/PY, PRY, AY AND L5

FILE 'REGISTRY' ENTERED ON 15 JAN 2008

=> D L4 QUE STAT

L1 STR



VAR G1=13/17/16 NODE ATTRIBUTES: DEFAULT MLEVEL IS ATOM DEFAULT ECLEVEL IS LIMITED

GRAPH ATTRIBUTES: RING(S) ARE ISOLATED OR EMBEDDED NUMBER OF NODES IS 18

STEREO ATTRIBUTES: NONE L2. SCR 2043

L4 25 SEA FILE=REGISTRY SSS FUL L1 AND L2

100.0% PROCESSED 2969 ITERATIONS SEARCH TIME: 00.00.01

25 ANSWERS

=> FILE ZCA FILE 'ZCA' ENTERED ON 15 JAN 2008 USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT. PLEASE SEE "HELP USAGETERMS" FOR DETAILS. COPYRIGHT (C) 2008 AMERICAN CHEMICAL SOCIETY (ACS)

## => D L6 1-6 CBIB ABS HITSTR HITRN

L6 ANSWER 1 OF 6 ZCA COPYRIGHT 2008 ACS on STN

142:363804 Lactone-containing polymers, resist materials containing them with low line edge roughness and excellent resolution, etching resistance, and thermal stability, and pattern formation using them. Funatsu, Akiyuki; Nishi, Tsunehiro; Nagura, Shigehiro (Shin-Etsu Chemical Industry Co., Ltd., Japan). Jpn. Kokai Tokkyo Koho JP. 2005097533 A 20050414, 58 pp. (Japanese). CODEN: JKXXAF. APPLICATION: JP 2004-144569 20040514. PRIORITY: JP 2003-311056 20030903.

The polymers, useful for excimer laser photolithog. or electron beam lithog., have repating units CH2CR1(CO2Z), CH2CR3(CO2Y), and CH2CR4(CO2X) (R1,3,4 = H, Me; X = lactone-contg. group; Y = 3-OH-5-R5-6-R6-adamantyl; Z = 1-R2-cyclopentyl, 1-R2-cyclohexyl; R2 = C1-12 linear, branched, or cyclic alkyl; R5,6 = H, OH).

IT 849060-37-3 849060-39-5

(lactone-contg. polymers for resists with low line edge roughness and good resoln., etching/resistance, and thermal stability)

RN 849060-37-3 ZCA

CN 2-Propenoic acid, 2-methyl-, dihydro-2'oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl ester,
polymer with dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)furan]-5(or 6)-yl 2-methyl-2-propenoate, 1-ethylcyclopentyl
2-methyl-2-propenoate and 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl
2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 848143-98-6 CMF C14 H18 O4 CCI IDS

CRN 848143-97-5 CMF C14 H18 O4 CCI IDS

CM 3

CRN 266308-58-1 CMF C11 H18 O2

CM 4

CRN 115372-36-6 CMF C14 H20 O3

RN 849060-39-5 ZCA

CN 2-Propenoic acid, 2-methyl-, 1-ethylcyclopentyl ester, polymer with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl 2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl 2-propenoate and 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 849060-38-4 CMF C13 H16 O4 CCI IDS

CM 2

CRN 581096-14-2 CMF C13 H16 O4 CCI IDS

CRN 266308-58-1 CMF C11 H18 O2

CM 4

CRN 216581-76-9 CMF C13 H18 O3

# IT 849060-37-3 849060-39-5

(lactone-contg. polymers for resists with low line edge roughness and good resoln., etching resistance, and thermal stability)

L6 ANSWER 2 OF 6 ZCA COPYRIGHT 2008 ACS on STN 142:325926 Polymer, resist composition and patterning process.

Tachibana, Seiichiro; Nishi, Tsunehiro; Kobayashi, Tomohiro (Japan). U.S. Pat. Appl. Publ. US 2005058938 A1 20050317, 46 pp. (English). CODEN: USXXCO: APPLICATION: US 2004-936753 20040909. PRIORITY: JP 2003-320659 20030912.

GΙ

- \* STRUCTURE DIAGRAM TOO LARGE FOR DISPLAY AVAILABLE VIA OFFLINE PRINT \*
- AB A polymer comprises recurring units of formulas I, II, III, IV (R1-3,4,7 = H, Me; R2 = acid labile group; R5,6 = H, hydroxyl; R8 = lactone structure group) and has a Mw of 1,000-50,000. A resist compn. comprising the inventive polymer has a sensitivity to high-energy radiation, improved resoln. and etching resistance and lends itself to lithog. micropatterning with electron beams or deep UV.
- IT 848143-99-7P 848144-00-3P 848144-01-4P 848144-02-5P 848144-03-6P

(polymer, resist compn. for patterning process)

RN 848143-99-7 ZCA

CN 2-Propenoic acid, 2-methyl-, polymer with dihydro-2'oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl
2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane2,3'(2'H)-furan]-5(or 6)-yl 2-methyl-2-propenoate,
3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-methyl-2-propenoate and
2-methyltricyclo[3.3.1.13,7]dec-2-yl 2-methyl-2-propenoate (9CI)
(CA INDEX NAME)

CM 1

CRN 848143-98-6 CMF C14 H18 O4 CCI IDS

CRN 848143-97-5 CMF C14 H18 O4

CCI IDS

CM 3

CRN 177080-67-0 CMF C15 H22 O2

CM 4

CRN 115372-36-6 CMF C14 H20 O3

CRN 79-41-4 CMF C4 H6 O2

$$\begin{array}{c} \text{CH}_2 \\ || \\ \text{Me-C-CO}_2 \text{H} \end{array}$$

RN 848144-00-3 ZCA

CN 2-Propenoic acid, 2-methyl-, polymer with dihydro-2'oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl
2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane2,3'(2'H)-furan]-5(or 6)-yl 2-methyl-2-propenoate,
2-ethyltricyclo[3.3.1.13,7]dec-2-yl 2-methyl-2-propenoate and
3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-methyl-2-propenoate (9CI)
(CA INDEX NAME)

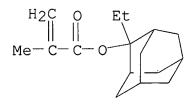
CM 1

CRN 848143-98-6 CMF C14 H18 O4 CCI IDS

CM 2

CRN 848143-97-5 CMF C14 H18 O4 CCI IDS

CRN 209982-56-9 CMF C16 H24 O2



CM 4

CRN 115372-36-6 CMF C14 H20 O3

CM 5

CRN 79-41-4 CMF C4 H6 O2

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\begin{array}{c} \text{CH}_2 \\ || \\ \text{Me-C-CO}_2 \text{H} \end{array}
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RN 848144-01-4 ZCA

CN 2-Propenoic acid, 2-methyl-, polymer with dihydro-2'oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl
2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane2,3'(2'H)-furan]-5(or 6)-yl 2-methyl-2-propenoate,
2-ethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate and
3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-methyl-2-propenoate (9CI)
(CA INDEX NAME)

CM 1

CRN 848143-98-6 CMF C14 H18 O4 CCI IDS

CM 2

CRN 848143-97-5 CMF C14 H18 O4 CCI IDS

CRN 330595-98-7 CMF C13 H20 O2

CM 4

CRN 115372-36-6 CMF C14 H20 O3

CM 5

CRN 79-41-4 CMF C4 H6 O2

RN 848144-02-5 ZCA
CN 2-Propenoic acid, 2-methyl-, polymer with dihydro-2'oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl
2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane2,3'(2'H)-furan]-5(or 6)-yl 2-methyl-2-propenoate,
2-ethyldecahydro-1,4:5,8-dimethanonaphthalen-2-yl
2-methyl-2-propenoate and 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl
2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 848143-98-6 CMF C14 H18 O4 CCI IDS

CM 2

CRN 848143-97-5 CMF C14 H18 O4 CCI IDS

$$\begin{array}{c|c} ^{H_2C} & \text{O} \\ \parallel & \parallel \\ \text{Me-} & \text{C-} & \text{C-} & \text{O-} & \text{D1} \end{array}$$

CRN 485819-03-2 CMF C18 H26 O2

CM 4

CRN 115372-36-6 CMF C14 H20 O3

CM 5

CRN 79-41-4 CMF C4 H6 O2

RN 848144-03-6 ZCA

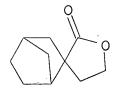
CN 2-Propenoic acid, 2-methyl-, polymer with dihydro-2'oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl
2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane2,3'(2'H)-furan]-5(or 6)-yl 2-methyl-2-propenoate,
3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-methyl-2-propenoate and
1-(7-oxabicyclo[2.2.1]hept-2-yl)cyclopentyl 2-methyl-2-propenoate
(9CI) (CA INDEX NAME)

CM 1

CRN 848143-98-6 CMF C14 H18 O4 CCI IDS

CM 2

CRN 848143-97-5 CMF C14 H18 O4 CCI IDS



CRN 676456-72-7 CMF C15 H22 O3

CM 4

CRN 115372-36-6 CMF C14 H20 O3

CM 5

CRN 79-41-4

CMF C4 H6 O2

IT 848143-99-7P 848144-00-3P 848144-01-4P 848144-02-5P 848144-03-6P

(polymer, resist compn. for patterning process)

L6 ANSWER 3 OF 6 ZCA COPYRIGHT 2008 ACS on STN 142:123189 Positive resist composition and method for forming resist pattern using same. Hada, Hideo; Miyairi, Miwa; Iwai, Takeshi (Tokyo Ohka Kogyo Co., Ltd., Japan). PCT Int. Appl. WO 2005003193 A1 20050113, 44 pp. DESIGNATED STATES: W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW; RW: AT, BE, BF, BJ, CF, CG, CH, CI, CM, CY, DE, DK, ES, FI, FR, GA, GB, GR, IE, IT, LU, MC, ML, MR, NE, NL, PT, SE, SN, TD, TG, TR. (Japanese). CODEN: PIXXD2. APPLICATION: WO 2004-JP9620 20040630. PRIORITY: JP 2003-192895 20030707; JP 2004-100204 20040330.

GΙ

PALO. FAV.

- \* STRUCTURE DIAGRAM TOO LARGE FOR DISPLAY AVAILABLE VIA OFFLINE PRINT \*
- AB A resist compn. is disclosed which enables to prevent surface roughening of a resist pattern after either etching or developing, or preferably after both etching and developing. A resist pattern is formed by using a pos. resist compn. comprising a resin component (A), an acid-forming agent component (B) which produces an acid when exposed, and an org. solvent (C). The resin component (A) contains at least one constitutional unit (al) contg. lactone which is represented by one of general formulas I-IV: (R = H, Me; m = 0, 1), and the alkali soly. thereof is increased by the action of an acid.
- IT 823810-78-2P 823810-79-3P 823810-80-6P 823817-70-5P

(resin in pos. resist compn.)

- RN 823810-78-2 ZCA
- CN 2-Propenoic acid, 2-methyl-, dihydro-2'- oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl ester, polymer

with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl 2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl 2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl 2-methyl-2-propenoate and 2-methyltricyclo[3.3.1.13,7]dec-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 479072-43-0 CMF C14 H18 O4

CM 2

CRN 479072-42-9 CMF C14 H18 O4

$$\begin{array}{c|c} H_2C & O \\ \parallel & \parallel \\ Me-C-C-O \end{array}$$

CM 3

CRN 479072-41-8 CMF C14 H18 O4

CRN 479072-40-7 CMF C14 H18 O4

CM 5

CRN 177080-67-0 CMF C15 H22 O2

RN 823810-79-3 ZCA
CN 2-Propenoic acid, 2-methyl-, dihydro-2'oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl ester, polymer
with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl
2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane2,3'(2'H)-furan]-5-yl 2-methyl-2-propenoate, dihydro-5'oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl
2-methyl-2-propenoate and 2-ethyltricyclo[3.3.1.13,7]dec-2-yl
2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 479072-43-0 CMF C14 H18 O4

CRN 479072-42-9 CMF C14 H18 O4

CM 3

CRN 479072-41-8 CMF C14 H18 O4

CM 4

CRN 479072-40-7 CMF C14 H18 O4

CM 5

CRN 209982-56-9 CMF C16 H24 O2

RN 823810-80-6 ZCA

CN 2-Propenoic acid, 2-methyl-, dihydro-2'oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl ester, polymer
with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl
2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane2,3'(2'H)-furan]-5-yl 2-methyl-2-propenoate, dihydro-5'oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl
2-methyl-2-propenoate and 2-ethyltricyclo[3.3.1.13,7]dec-2-yl
2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 479072-43-0 CMF C14 H18 O4

$$\begin{array}{c|c} H_2C & O \\ \parallel & \parallel \\ Me-C-C-O \end{array}$$

CM 2

CRN 479072-42-9 CMF C14 H18 O4

CM 3

CRN 479072-41-8

CMF C14 H18 O4

CM 4

CRN 479072-40-7 CMF C14 H18 O4

CM 5

CRN 303186-14-3 CMF C15 H22 O2

RN 823817-70-5 ZCA

CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, decahydro-6(or 7)-[(1-oxo-2-propenyl)oxy]-, 1,1-dimethylethyl ester, polymer with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl 2-propenoate, dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl 2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl 2-propenoate and dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl 2-propenoate (9CI) (CA INDEX NAME)

CRN 479072-47-4 CMF C13 H16 O4

CM 2

CRN 479072-46-3 CMF C13 H16 O4

CM 3

CRN 479072-45-2 CMF C13 H16 O4

CM · 4

CRN 479072-44-1 CMF C13 H16 O4

CRN 217652-52-3 CMF C20 H28 O4 CCI IDS

IT 823810-78-2P 823810-79-3P 823810-80-6P 823817-70-5P

(resin in pos. resist compn.)

L6 ANSWER 4 OF 6 ZCA COPYRIGHT 2008 ACS on STN
141:417915 Preparation of hydroxy oxide compound, negative-working resist using it, and, manufacture of wiring. Yokoyama, Yoshiyuki; Hattori, Takashi; Iwashita, Atsushi; Tachikawa, Toshikazu (Tokyo Ohka Kogyo Co., Ltd., Japan; Hitachi Ltd.). Jpn. Kokai Tokkyo Koho JP 2004317575 A 2004[1][1], 17 pp. (Japanese). CODEN: JKXXAF. APPLICATION: JP 2003-107908 20030411.

GΙ

The hydroxy oxide compd. is obtained by the steps of (i) removing metal impurity in a compd. (A) bearing lactone group in the side chain and (ii) opening the lactone ring of the compd. A by hydrolysis using an org. alk. compd. Neg.-working resist compn. contains the hydroxy oxide compd. The hydroxy oxide compd. may I (A = N, S, C1-21 alkyl), for example. The wiring is manufd. by the steps of (1) forming a layer of the neg. resist contg. resin contg. the hydroxy oxide and an acid generator, (2) exposing and developing the resist for pattern formation, (3) etching the substrate by using the pattern as a mask, and (4) removing the residual resist pattern. As metal impurity content is lowered and clear resist pattern is obtained.

IT **790665-51-9DP**, hydrolyzed

(neg. resist contg. purified hydroxy oxide compd. prepd. by hydrolysis of lactone ring by org. alk. compd.)

RN 790665-51-9 ZCA

CN 2-Propenoic acid, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl ester, homopolymer (9CI) (CA INDEX NAME)

CM 1

CRN 479072-47-4

CMF C13 H16 O4

#### IT **790665-51-9P**

(purifn. and hydrolysis of; neg. resist contg. purified hydroxy oxide compd. prepd. by hydrolysis of lactone ring by org. alk. compd.)

RN 790665-51-9 ZCA

CN 2-Propenoic acid, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl ester, homopolymer (9CI) (CA INDEX NAME)

CM 1

CRN 479072-47-4 CMF C13 H16 O4

## IT **790665-51-9DP**, hydrolyzed

(neg. resist contg. purified hydroxy oxide compd. prepd. by hydrolysis of lactone ring by org. alk. compd.)

# IT 790665-51-9P

(purifn. and hydrolysis of; neg. resist contg. purified hydroxy oxide compd. prepd. by hydrolysis of lactone ring by org. alk. compd.)

- L6 ANSWER 5 OF 6 ZCA COPYRIGHT 2008 ACS on STN
- 141:358084 Negative-working resist material and patterning method.
  Iwashita, Atsushi; Tachikawa, Toshikazu (Tokyo Ohka Kogyo Co., Ltd.,
  Japan). Jpn. Kokai Tokkyo Koho JP 2004294638 A 20041021, 19 pp.
  (Japanese). CODEN: JKXXAF. APPLICATION: JP 2003-84981 20030326.
- AB Disclosed is the neg.-working resist material comprising a polymer compd. and a photoacid, wherein the polymer compd. has a polymerizable unit bonded to the backbone chain via C of a hydroxy acid and has no space between the hydroxy acid and the backbone chain not to admit an alkali substance close to it. The hydroxy acid group bonded to the backbone chain improved the storage stability and the space resoln.
- IT 776329-02-3P 776329-03-4P

(neg.-working resist material having hydroxy acid group bonded to backbone chain)

RN 776329-02-3 ZCA

CN 2-Propenoic acid, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl ester, polymer with dihydro-4,4-dimethyl-3-methylene-2(3H)-furanone and 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 479072-47-4 CMF C13 H16 O4

present (3)

CM 2

CRN 216581-76-9 CMF C13 H18 O3

CM 3

CRN 135102-85-1 CMF C7 H10 O2

RN 776329-03-4 ZCA

CN 2-Propenoic acid, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-

2,3'(2'H)-furan]-5-yl ester, polymer with hexahydro-2-oxo-3,5-methano-2H-cyclopenta[b]furan-6-yl 2-propenoate and 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 479072-47-4 CMF C13 H16 O4

CM 2

CRN 242129-35-7 CMF C11 H12 O4

CM 3

CRN 216581-76-9 CMF C13 H18 O3

## IT 776329-02-3P 776329-03-4P

(neg.-working resist material having hydroxy acid group bonded to

backbone chain)

L6 ANSWER 6 OF 6 ZCA COPYRIGHT 2008 ACS on STN

139:188311 Positive DUV resist compositions with suppressed roughness of etched surfaces and good dissolution and defocus latitude in contact hole pattern formation. Sato, Kenichiro (Fuji Photo Film Co., Ltd., Japan). Jpn. Kokai Tokkyo Koho JP 2003233187 A 20030822, 54 pp. (Japanese). CODEN: JKXXAF. APPLICATION: JP 2002-32448 20020208.

GΙ

The pos. resist compns. contain (A) 2 resins contg. specific AΒ repeating units bearing alicyclic groups and (B) compds. which generate acids by irradn. of actinic ray or radiation. A comprise (A1) resins bearing repeating untis represented by CH2CR1ACO2ALG [R1 = H, Me; A = single bond, linkage; ALG = I, CR12R13R14, CH(OR15)R16, II, and CR22R25CHR23COR24; R11 = Me, Et, n-Pr, i-Pr, n-Bu, sec-Bu; Z = atom. group necessary for forming alicyclic hydrocarbyl (ACHC) together with C; R12-R16 = C1-4 alkyl, ACHC;  $\geq$ 1 of R12-R14 and R15 and/or R16 show ACHC; R17-R21 = H, C1-4 alkyl, alkcyclic hydrocarbyl; ≥1 of R17-R21 show ACHC; R19 and/or R21 = C1-4 alkyl, ACHC; R22-R25 = C1-4 alkyl, alicyclic hydrocarbyl; ≥1 of R22-R25 = ACHC; R23 and R24 may be bonded to each other and form ring] and (A2) resins bearing repeating units represented by CH2CR2CO2A1R3A2CO2R4 (R2 = H, alkyl; R3 = ACHC; R4 = chain-type tertiary alkyl, 1-alkoxyalkyl, tetrahydropyranyl, tetrahydrofuranyl; A1, A2 = single bond, alkylene, ether, carbonyl, ester).

IT 581096-15-3P 581096-72-2P

(pos. DUV resist compns. with suppressed roughness of etched surfaces and good dissoln. and defocus latitude in contact hole pattern formation)

RN 581096-15-3 ZCA

CN Tricyclo[3.3.1.13,7]decane-1-carboxylic acid, 3-[(2-methyl-1-oxo-2-propenyl)oxy]-, 1,1-dimethylpropyl ester, polymer with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl 2-propenoate and 3-hydroxy-5-methyltricyclo[3.3.1.13,7]dec-1-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CRN 581096-14-2 CMF C13 H16 O4

CCI IDS

CM 2

CRN 581096-13-1 CMF C20 H30 O4

CM 3

CRN 476312-25-1 CMF C15 H22 O3

RN 581096-72-2 ZCA

CN 2-Propenoic acid, 2-methyl-, 5-ethyloctahydro-4,7-methano-1H-inden-5-yl ester, polymer with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl 2-propenoate and 2-[[octahydro-1,2(or 2,3)-dihydroxy-4,7-methano-1H-inden-5-yl]oxy]ethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 581096-14-2 CMF C13 H16 O4 CCI IDS

CM 2

CRN 348089-09-8 CMF C16 H24 O2

CRN 140919-18-2

CMF C15 H22 O5

CCI IDS

$$H_2C = CH - C - O - CH_2 - CH_2 - O$$
 OH

D1-OH

# IT 581096-15-3P 581096-72-2P

(pos. DUV resist compns. with suppressed roughness of etched surfaces and good dissoln. and defocus latitude in contact hole pattern formation)